

**April 2009** 

# MOC223M

# **Small Outline Optocouplers Darlington Output**

## **Features**

- U.L. Recognized (File #E90700, Volume 2)
- VDE Recognized (File #136616) (add option "V" for VDE approval, i.e, MOC223VM)
- Industry Standard SOIC-8 Surface Mountable Package with 0.050" lead spacing
- High Current Transfer Ratio of 500% Minimum at I<sub>F</sub> = 1mA
- Standard SOIC-8 Footprint, with 0.050" Lead Spacing
- Compatible with Dual Wave, Vapor Phase and IR Reflow Soldering
- High Input-Output Isolation Voltage of 2500 V<sub>AC(rms)</sub> Guaranteed

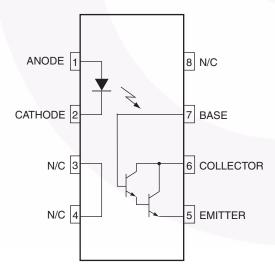
## **Applications**

- Low power logic circuits
- Interfacing and coupling systems of different potentials and impedances
- Telecommunications equipment
- Portable electronics
- Solid state relays

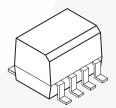
## Description

The MOC223M consists of a gallium arsenide infrared emitting diode optically coupled to a monolithic silicon photodarlington detector, in a surface mountable, small outline, plastic package. It is ideally suited for high density applications, and eliminates the need for through the board mounting.

## **Schematic**



# **Package Outline**



**Absolute Maximum Ratings** ( $T_A = 25^{\circ}$ C Unless otherwise specified) Stresses exceeding the absolute maximum ratings may damage the device. The device may not function or be operable above the recommended operating conditions and stressing the parts to these levels is not recommended. In addition, extended exposure to stresses above the recommended operating conditions may affect device reliability. The absolute maximum ratings are stress ratings only.

Symbol	Rating	Value	Unit	
EMITTER			1	
I <sub>F</sub>	Forward Current - Continuous	60	mA	
I <sub>F</sub> (pk)	Forward Current – Peak (PW = 100µs, 120pps)	1.0	А	
V <sub>R</sub>	Reverse Voltage	6.0	V	
P <sub>D</sub>	LED Power Dissipation @ T <sub>A</sub> = 25°C Derate above 25°C	90 0.8	mW mW/°C	
DETECTOR			!	
V <sub>CEO</sub>	Collector-Emitter Voltage	30	V	
V <sub>ECO</sub>	Emitter-Collector Voltage	7.0	V	
V <sub>CBO</sub>	Collector-Base Voltage	70	V	
I <sub>C</sub>	Collector Current-Continuous	150	mA	
$P_{D}$	Detector Power Dissipation @ T <sub>A</sub> = 25°C Derate above 25°C	150 1.76	mW mW/°C	
TOTAL DEVICE				
V <sub>ISO</sub>	Input-Output Isolation Voltage (f = 60Hz, t = 1 min.)	2500	Vac(rms)	
$P_{D}$	Total Device Power Dissipation @ T <sub>A</sub> = 25°C Derate above 25°C	250 2.94	mW mW/°C	
T <sub>A</sub>	Ambient Operating Temperature Range	-40 to +100	°C	
T <sub>stg</sub>	Storage Temperature Range	-40 to +150	°C	

# **Electrical Characteristics** (T<sub>A</sub> = 25°C unless otherwise specified)

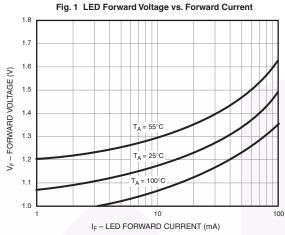
Symbol	Parameter	Test Conditions	Min.	Тур.*	Max.	Unit
EMITTER					I	
V <sub>F</sub>	Input Forward Voltage	I <sub>F</sub> = 1.0mA		1.08	1.3	V
I <sub>R</sub>	Reverse Leakage Current	V <sub>R</sub> = 6.0V		0.001	100	μΑ
C <sub>IN</sub>	Input Capacitance			18		pF
DETECTO	R			'		
I <sub>CEO1</sub>	Collector-Emitter Dark Current	$V_{CE} = 5.0 \text{ V}, T_{A} = 25^{\circ}\text{C}$		1.0	50	nA
I <sub>CEO2</sub>		$V_{CE} = 5.0 \text{ V}, T_{A} = 100^{\circ}\text{C}$		10		μA
BV <sub>CEO</sub>	Collector-Emitter Breakdown Voltage	I <sub>C</sub> = 100μA	30	100		V
BV <sub>ECO</sub>	Emitter-Collector Breakdown Voltage	I <sub>E</sub> = 100μA	7.0	10		V
C <sub>CE</sub>	Collector-Emitter Capacitance	f = 1.0 MHz, V <sub>CE</sub> = 0		5.5		pF
COUPLED						
CTR	Current Transfer Ratio <sup>(3)</sup>	I <sub>F</sub> = 1.0mA, V <sub>CE</sub> = 5.0V	500	1000		%
V <sub>ISO</sub>	Isolation Surge Voltage <sup>(1,2)</sup>	f = 60Hz AC Peak, t = 1 min.	2500			Vac(rms)
R <sub>ISO</sub>	Isolation Resistance <sup>(2)</sup>	V = 500V	10 <sup>11</sup>			Ω
V <sub>CE (sat)</sub>	Collector-Emitter Saturation Voltage	$I_C = 500\mu A, I_F = 1.0mA$			1.0	V
C <sub>ISO</sub>	Isolation Capacitance <sup>(2)</sup>	V <sub>I-O</sub> = 0V, f = 1MHz		0.2		pF
t <sub>on</sub>	Turn-On Time	$I_F = 5.0 \text{mA}, V_{CC} = 10 \text{V}, R_L = 100 \Omega$ (Fig. 6)		10		μs
t <sub>off</sub>	Turn-Off Time	$I_F = 5.0 \text{mA}, V_{CC} = 10 \text{V}, R_L = 100 \Omega$ (Fig. 6)		125		ns
t <sub>r</sub>	Rise Time	$I_F = 5.0 \text{mA}, V_{CC} = 10 \text{V}, R_L = 100 \Omega$ (Fig. 6)		8		μs
t <sub>f</sub>	Fall Time	$I_F = 5.0 \text{mA}, V_{CC} = 10 \text{V}, R_L = 100 \Omega$ (Fig. 6)		110		μs

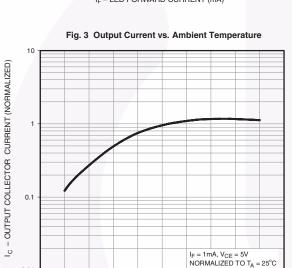
<sup>\*</sup>All typicals at T<sub>A</sub> = 25°C

## Notes:

- 1. Isolation Surge Voltage,  $V_{\text{ISO}}$ , is an internal device dielectric breakdown rating.
- 2. For this test, Pins 1 and 2 are common and Pins 5, 6 and 7 are common.
- 3. Current Transfer Ratio (CTR) =  $I_C / I_F x$  100%.

# **Typical Performance Curves**





T<sub>A</sub> – AMBIENT TEMPERATURE (°C)

Fig. 2 Output Curent vs. Input Current

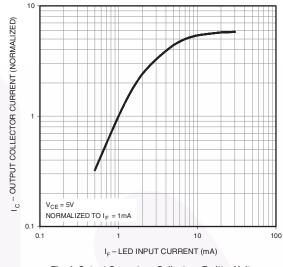


Fig. 4 Output Current vs. Collector - Emitter Voltage

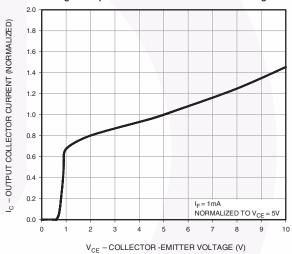
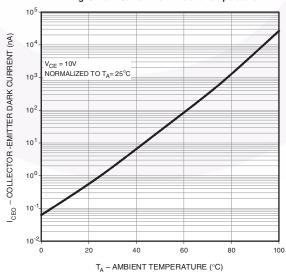


Fig. 5 Dark Current vs. Ambient Temperature

100



-80 -60 -40

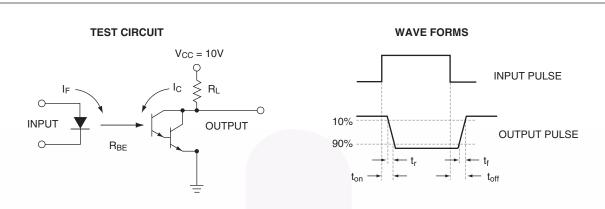
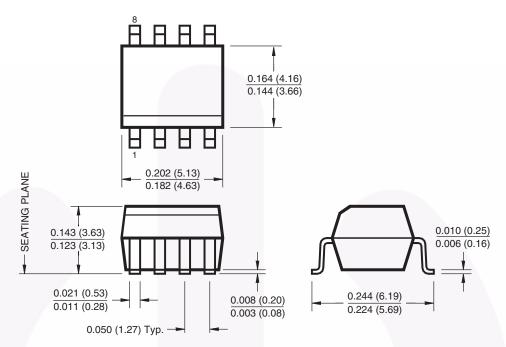


Figure 6. Switching Time Test Circuit and Waveform

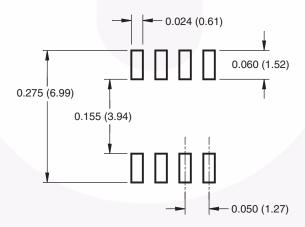
## **Package Dimensions**

## 8-pin SOIC Surface Mount



Lead Coplanarity: 0.004 (0.10) MAX

## **Recommended Pad Layout**



Dimensions in inches (mm).

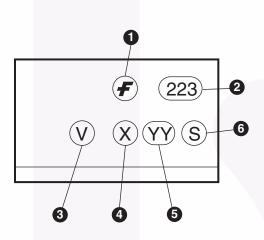
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# **Ordering Information**

Option	Order Entry Identifier	Description	
V	V	VDE 0884	
R2	R2	Tape and reel (2500 units per reel)	
R2V	R2V	VDE 0884, Tape and reel (2500 units per reel)	

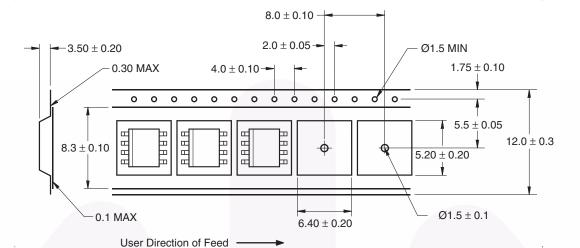
# **Marking Information**



Defini	tions	
1	Fairchild logo	
2	Device number	
3	VDE mark (Note: Only appears on parts ordered with VDE option – See order entry table)	
4	One digit year code, e.g., '3'	
5	Two digit work week ranging from '01' to '53'	
6	Assembly package code	

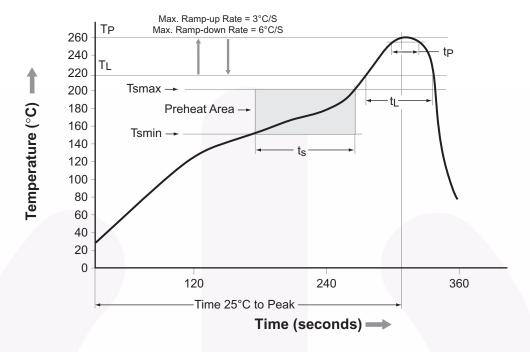
<sup>\*</sup>Note – 'V' option parts marked with date code '325' or earlier are marked in portrait format.

# **Carrier Tape Specifications**



Dimensions in mm

# **Reflow Profile**



Profile Freature	Pb-Free Assembly Profile	
Temperature Min. (Tsmin)	150°C	
Temperature Max. (Tsmax)	200°C	
Time (t <sub>S</sub> ) from (Tsmin to Tsmax)	60-120 seconds	
Ramp-up Rate (t <sub>L</sub> to t <sub>P</sub> )	3°C/second max.	
Liquidous Temperature (T <sub>L</sub> )	217°C	
Time (t <sub>L</sub> ) Maintained Above (T <sub>L</sub> )	60–150 seconds	
Peak Body Package Temperature	260°C +0°C / -5°C	
Time (t <sub>P</sub> ) within 5°C of 260°C	30 seconds	
Ramp-down Rate (T <sub>P</sub> to T <sub>L</sub> )	6°C/second max.	
Time 25°C to Peak Temperature	8 minutes max.	





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